NSN 5961-00-854-8470

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-854-8470 **Inclosure Material:** Glass **Overall Length:** Between 0.195 inches and 0.300 inches **Terminal Length:** Between 1.000 inches and 1.500 inches **Overall Diameter:** Between 0.078 inches and 0.107 inches **Mounting Method:** Terminal **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 200.0 breakdown voltage, dc and 175.0 working peak reverse voltage **Current Rating Per Characteristic:** 100.00 milliamperes forward current, total rms megahertz **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** Nuclear hardness critical items: no drawing to determine if isc code 1 item should also be nuclear hardness. Can't change criticality code to reflect nuclear hardness **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-prf-19500/169 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0

Mil-prf-19500 spec.

Mil-std (military Standard):